

10/732,962

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/139987	USPAT	OR	ON	2005/06/24 10:58
L2	1	L1 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides)	USPAT	OR	ON	2005/06/24 11:13
L3	5	(nitridation adj receptive adj material) and (nitridation adj resistive adj material) and silicon and dioxide and oxide	USPAT	OR	ON	2005/06/24 11:16
L4	1	("6852081").PN.	USPAT	OR	OFF	2005/06/24 11:13
L5	0	4 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides)	USPAT	OR	ON	2005/06/24 11:13
L6	1	4 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides or uniform or tantalum or thick or thickness or chemisorption)	USPAT	OR	ON	2005/06/24 11:16
L7	1	("6825081").PN.	USPAT	OR	OFF	2005/06/24 11:16
L8	1	7 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides or uniform or tantalum or thick or thickness or chemisorption)	USPAT	OR	ON	2005/06/24 11:18

L9	5	3 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides or uniform or tantalum or thick or thickness or chemisorption)	USPAT	OR	ON	2005/06/24 11:26
L10	1	("6787834").PN.	USPAT	OR	OFF	2005/06/24 11:26
L11	1	10 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides or uniform or tantalum or thick or thickness or chemisorption)	USPAT	OR	ON	2005/06/24 11:28
L12	1	("6235571").PN.	USPAT	OR	OFF	2005/06/24 11:28
L13	1	12 and (semiconductor or assembly or nitridation or receptive or material or resistive or silicon or dioxide or oxide or monolayer or directly or HSG or polysilicon or hemispherical or grained or silicon or BPSG or boron or phospho or silica or oxides or uniform or tantalum or thick or thickness or chemisorption)	USPAT	OR	ON	2005/06/24 11:38
L14	1492	257/310	USPAT	OR	ON	2005/06/24 11:38
L15	198	257/646	USPAT	OR	ON	2005/06/24 11:38
L16	451	257/649	USPAT	OR	ON	2005/06/24 11:38
L17	1010	257/288	USPAT	OR	ON	2005/06/24 11:38
L18	3674	257/296	USPAT	OR	ON	2005/06/24 11:38
L19	352	257/297	USPAT	OR	ON	2005/06/24 11:38
L20	1671	257/301	USPAT	OR	ON	2005/06/24 11:38
L21	1294	257/303	USPAT	OR	ON	2005/06/24 11:38
L22	751	257/304	USPAT	OR	ON	2005/06/24 11:38
L23	2929	257/306	USPAT	OR	ON	2005/06/24 11:38
S1	1	10/139987	USPAT	OR	ON	2005/06/24 10:11
S2	3	09/975879	USPAT	OR	ON	2005/06/24 10:55